

74HC245; 74HCT245

Octal bus transceiver; 3-state

Rev. 4 — 26 February 2016

Product data sheet

1. General description

The 74HC245; 74HCT245 is an 8-bit transceiver with 3-state outputs. The device features an output enable (\overline{OE}) and send/receive (DIR) for direction control. A HIGH on \overline{OE} causes the outputs to assume a high-impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

2. Features and benefits

- Complies with JEDEC standard JESD7A
- Input levels:
 - ◆ For 74HC245: CMOS level
 - ◆ For 74HCT245: TTL level
- Octal bidirectional bus interface
- Non-inverting 3-state outputs
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC245D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74HCT245D				
74HC245DB	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1
74HCT245DB				
74HC245PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74HCT245PW				
74HC245BQ	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DHVQFN20	plastic dual-in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85\text{ mm}$	SOT764-1
74HCT245BQ				



4. Functional diagram



Fig 1. Logic symbol



Fig 2. IEC logic symbol

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
DIR	1	direction control
A0, A1, A2, A3, A4, A5, A6, A7	2, 3, 4, 5, 6, 7, 8, 9	data input/output
GND	10	ground (0 V)
B7, B6, B5, B4, B3, B2, B1, B0	11, 12, 13, 14, 15, 16, 17, 18	data input/output
$\overline{\text{OE}}$	19	output enable input (active LOW)
V _{CC}	20	supply voltage

6. Functional description

6.1 Function table

Table 3. Function table^[1]

Input		Input/output	
OE	DIR	An	Bn
L	L	A = B	input
L	H	input	B = A
H	X	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_O	output current	$-0.5\text{ V} < V_O < V_{CC} + 0.5\text{ V}$	-	± 35	mA
I_{CC}	supply current		-	70	mA
I_{GND}	ground current		-70	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	SO20, SSOP20, TSSOP20 and DHVQFN20 packages ^[1]	-	500	mW

[1] For SO20 packages: above 70 °C, P_{tot} derates linearly with 8 mW/K.
 For SSOP20 and TSSOP20 packages: above 60 °C, P_{tot} derates linearly with 5.5 mW/K.
 For DHVQFN20 packages: above 60 °C, P_{tot} derates linearly with 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	74HC245			74HCT245			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC245										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
I _O = -7.8 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V		
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
I _O = 7.8 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V		
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _{CC} = 6.0 V; V _O = V _{CC} or GND	-	-	±0.5	-	±5.0	-	±10	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF
C _{I/O}	input/output capacitance		-	10	-	-	-	-	-	pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT245										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -6 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 6.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _{CC} = 5.5 V; V _O = V _{CC} or GND	-	-	±0.5	-	±5.0	-	±10	μA
I _{CC}	supply current	V _I = V _{CC} or GND; V _{CC} = 5.5 V; I _O = 0 A	-	-	8.0	-	80	-	160	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 2.1 V; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V; I _O = 0 A								
		An or Bn inputs	-	40	144	-	180	-	196	μA
		$\overline{\text{OE}}$ input	-	150	540	-	675	-	735	μA
		DIR input	-	90	324	-	405	-	441	μA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF
C _{I/O}	input/output capacitance		-	10	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics
GND = 0 V; for load circuit see Figure 7.

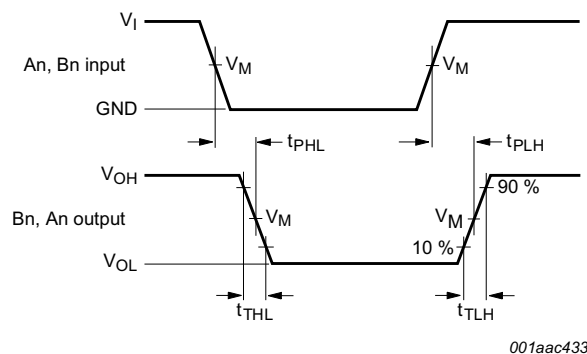
Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Max (85 °C)	Max (125 °C)	
74HC245								
t _{pd}	propagation delay	An to Bn or Bn to An; see Figure 5 [1]						
		V _{CC} = 2.0 V	-	25	90	115	135	ns
		V _{CC} = 4.5 V	-	9	18	23	27	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	7	-	-	-	ns
		V _{CC} = 6.0 V	-	7	15	20	23	ns
t _{en}	enable time	\overline{OE} to An or Bn; see Figure 6 [2]						
		V _{CC} = 2.0 V	-	30	150	190	225	ns
		V _{CC} = 4.5 V	-	11	30	38	45	ns
		V _{CC} = 6.0 V	-	9	26	33	38	ns
t _{dis}	disable time	\overline{OE} to An or Bn; see Figure 6 [3]						
		V _{CC} = 2.0 V	-	41	150	190	225	ns
		V _{CC} = 4.5 V	-	15	30	38	45	ns
		V _{CC} = 6.0 V	-	12	26	33	38	ns
t _t	transition time	see Figure 5 [4]						
		V _{CC} = 2.0 V	-	14	60	75	90	ns
		V _{CC} = 4.5 V	-	5	12	15	18	ns
		V _{CC} = 6.0 V	-	4	10	13	15	ns
C _{PD}	power dissipation capacitance	per buffer; V _I = GND to V _{CC} [5]	-	30	-	-	-	pF

Table 7. Dynamic characteristics ...continued
GND = 0 V; for load circuit see Figure 7.

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Max (85 °C)	Max (125 °C)	
74HCT245								
t _{pd}	propagation delay	An to Bn or Bn to An; see Figure 5 [1]						
		V _{CC} = 4.5 V	-	12	22	28	33	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	10	-	-	-	ns
t _{en}	enable time	\overline{OE} to An or Bn; see Figure 6 [2]	-	16	30	38	45	ns
t _{dis}	disable time	\overline{OE} to An or Bn; see Figure 6 [3]	-	16	30	38	45	ns
t _t	transition time	V _{CC} = 4.5 V; see Figure 5 [4]	-	5	12	15	18	ns
C _{PD}	power dissipation capacitance	per buffer; V _I = GND to V _{CC} - 1.5 V [5]	-	30	-	-	-	pF

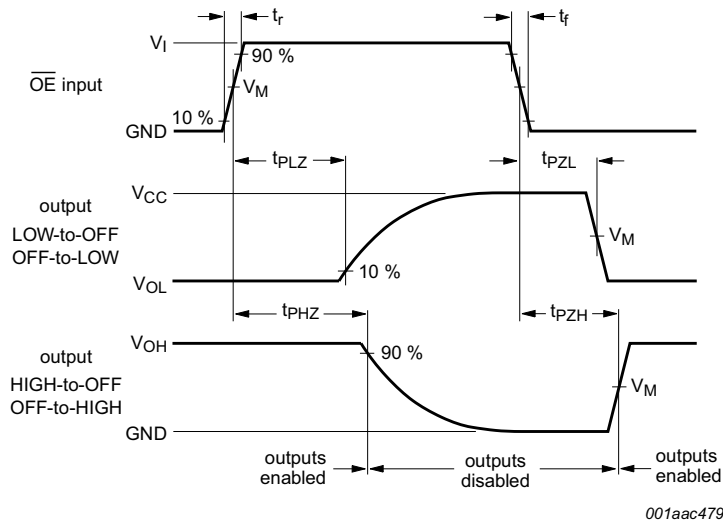
- [1] t_{pd} is the same as t_{PHL} and t_{PLH}.
- [2] t_{en} is the same as t_{PZH} and t_{PZL}.
- [3] t_{dis} is the same as t_{PHZ} and t_{PLZ}.
- [4] t_t is the same as t_{THL} and t_{TLH}.
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms



Measurement points are given in Table 8.
 V_{OL} and V_{OH} are typical voltage output drop that occur with the output load.

Fig 5. Input (An, Bn) to output (Bn, An) propagation delays and output transition times



Measurement points are given in [Table 8](#).
 VOL and VOH are typical voltage output drop that occur with the output load.

Fig 6. 3-state output enable and disable times

Table 8. Measurement points

Type	Input	Output
	VM	VM
74HC245	0.5VCC	0.5VCC
74HCT245	1.3 V	1.3 V



Test data is given in [Table 9](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 7. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC245	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74HCT245	3 V	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

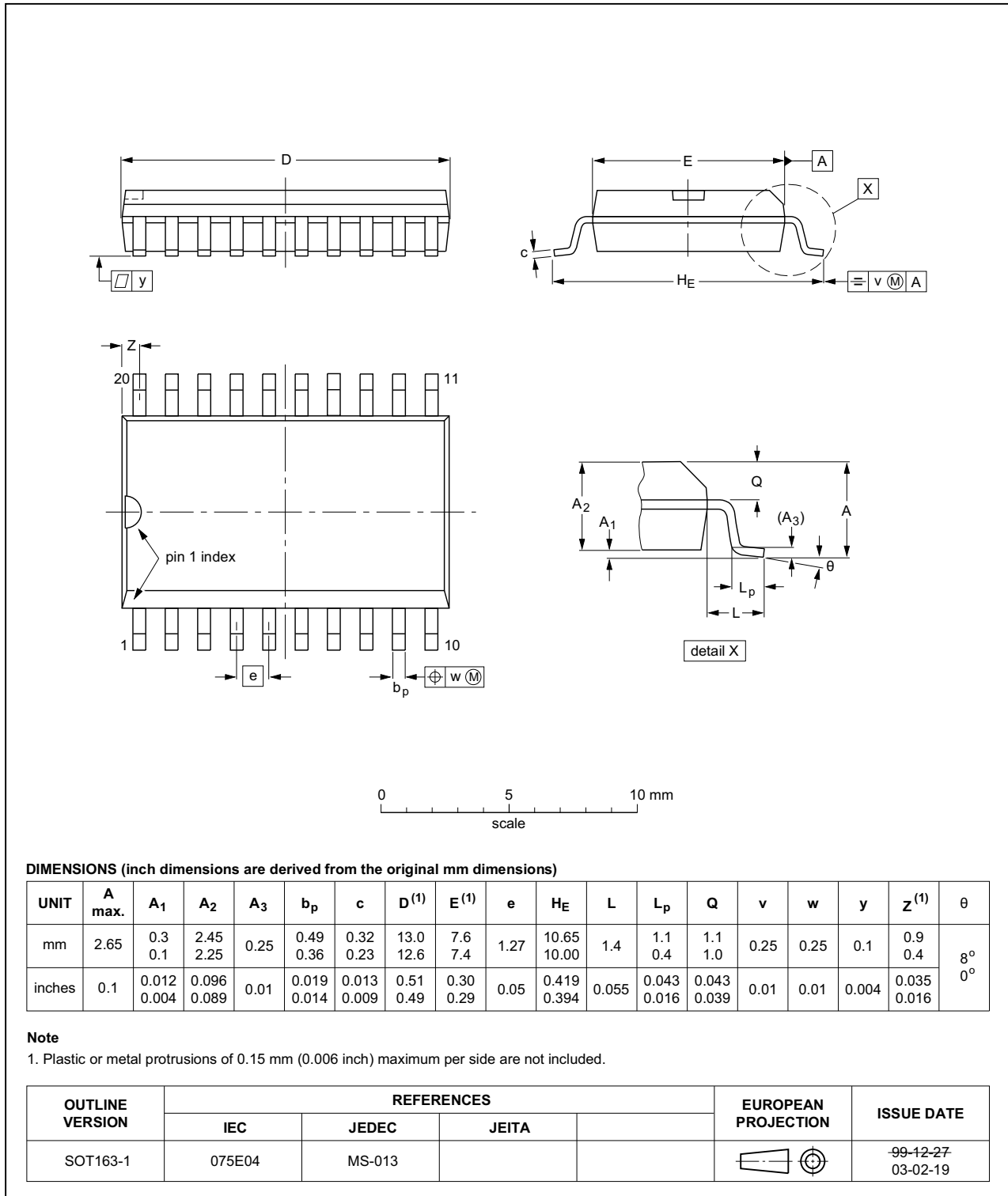


Fig 8. Package outline SOT163-1 (SO20)

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1

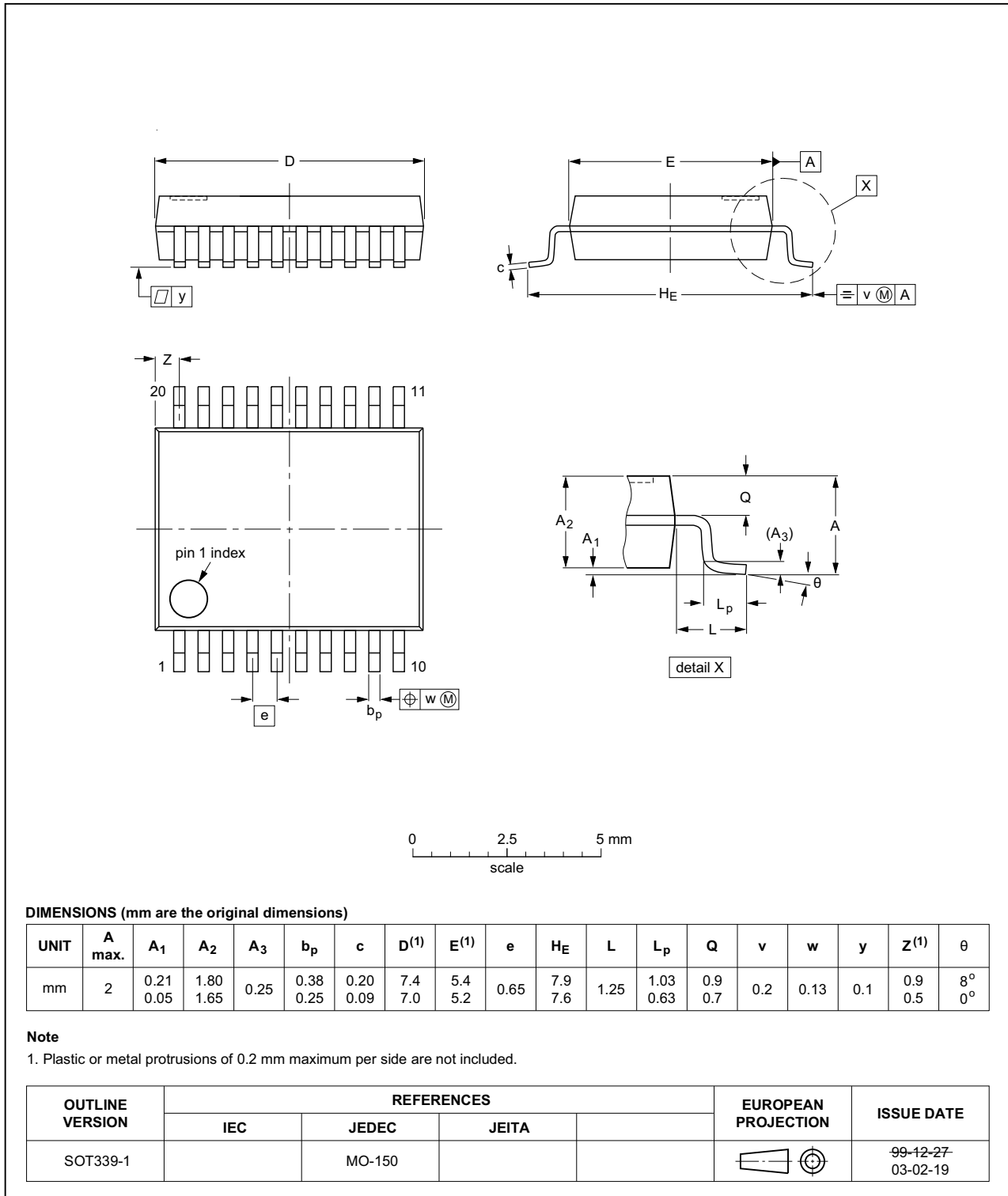


Fig 9. Package outline SOT339-1 (SSOP20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1



Fig 10. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm

SOT764-1



Fig 11. Package outline SOT764-1 (DHVQFN20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT245 v.4	20160226	Product data sheet	-	74HC_HCT245 v.3
Modifications:	<ul style="list-style-type: none"> Type numbers 74HC245N and 74HCT245N (SOT146-1) removed. 			
74HC_HCT245 v.3	20050131	Product data sheet	-	74HC_HCT245_CNV v.2
Modifications:	<ul style="list-style-type: none"> The format of this data sheet is redesigned to comply with the new presentation and information standard of Philips Semiconductors Section 3 "Ordering information", Section 5 "Pinning information" and Section 12 "Package outline" are modified to include the DHVQFN20 package. 			
74HC_HCT245_CNV v.2	19930930	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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